

H11AA1, H11AA2, H11AA3, H11AA4
H11AA1X, H11AA2X, H11AA3X, H11AA4X



**A.C. INPUT PHOTOTRANSISTOR
OPTICALLY COUPLED
ISOLATORS**

APPROVALS

- UL recognised, File No. E91231
- CSA recognised, Cert. No. CA 110306-1

'X' SPECIFICATION APPROVALS

- VDE0884 in 3 available lead form :-
- STD
- G form
- SMD approved to CECC 00802

DESCRIPTION

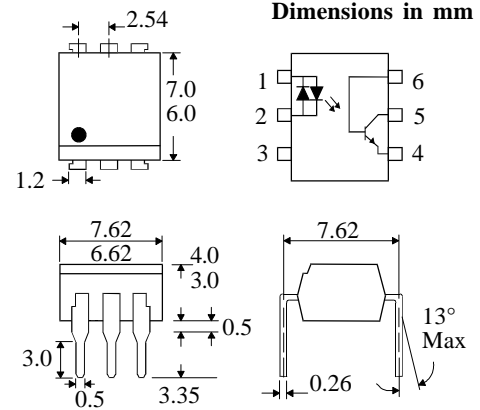
The H11AA series of optically coupled isolators consist of two infrared light emitting diodes connected in inverse parallel and NPN silicon photo transistor in a standard 6 pin dual in line plastic package.

FEATURES

- Options :-
10mm lead spread - add G after part no.
Surface mount - add SM after part no.
Tape&reel - add SMT&R after part no.
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- AC or polarity insensitive input
- All electrical parameters 100% tested
- Custom electrical selections available

APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Telephone sets, Telephone exchangers
- Signal transmission between systems of different potentials and impedances



**ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)**

Storage Temperature _____ -55°C to + 150°C
Operating Temperature _____ -55°C to + 100°C
Lead Soldering Temperature
(1/16 inch (1.6mm) from case for 10 secs) 260°C

INPUT DIODE

Forward Current _____ ±100mA
Peak Forward Current _____ ±1A
Power Dissipation _____ 200mW

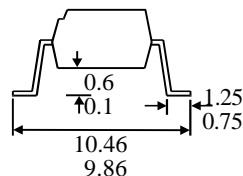
OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO} _____ 30V
Collector-base Voltage BV_{CBO} _____ 70V
Emitter-collector Voltage BV_{ECO} _____ 7V
Emitter-base Voltage BV_{EBO} _____ 5V
Power Dissipation _____ 300mW

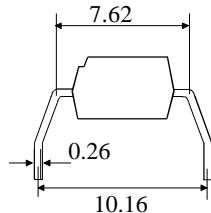
POWER DISSIPATION

Total Power Dissipation _____ 350mW
(derate linearly 4.67mW/°C above 25°C)

**OPTION SM
SURFACE MOUNT**



OPTION G



ISOCOM COMPONENTS LTD

Unit 25B, Park View Road West,
Park View Industrial Estate, Brenda Road
Hartlepool, TS25 1YD England Tel: (01429)863609
Fax: (01429) 863581 e-mail sales@isocom.co.uk
<http://www.isocom.com>

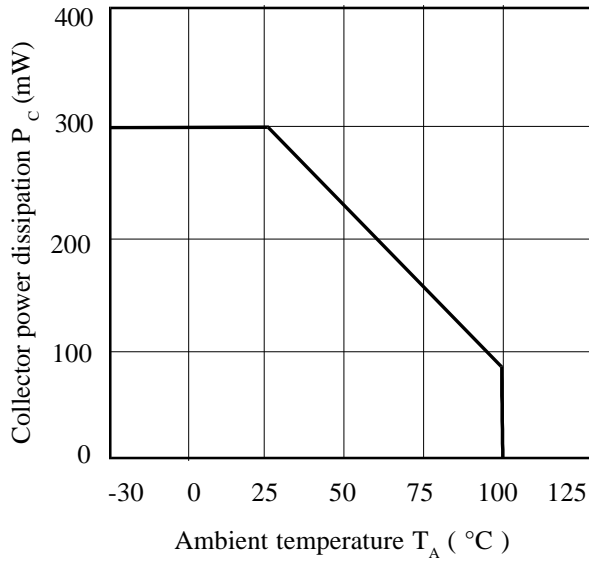
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.5	V	$I_F = \pm 10\text{mA}$
Output	Collector-emitter Breakdown (BV_{CEO}) (note 2)	30			V	$I_C = 1\text{mA}$
	Collector-base Breakdown (BV_{CBO})	70			V	$I_C = 100\mu\text{A}$
	Emitter-base Breakdown (BV_{EBO})	5			V	$I_E = 100\mu\text{A}$
	Emitter-collector Breakdown (BV_{ECO})	7			V	$I_E = 100\mu\text{A}$
	Collector-emitter Dark Current (I_{CEO})			50	nA	$V_{CE} = 10\text{V}$
Coupled	Current Transfer Ratio (CTR) (note 2)					
	H11AA4	100			%	$\pm 10\text{mA} I_F, 10\text{V } V_{CE}$
	H11AA3	50			%	$\pm 10\text{mA} I_F, 10\text{V } V_{CE}$
	H11AA1	20			%	$\pm 10\text{mA} I_F, 10\text{V } V_{CE}$
	H11AA2	10			%	$\pm 10\text{mA} I_F, 10\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.4	V	$\pm 10\text{mA} I_F, 0.5\text{mA} I_C$
	Current Transfer Ratio Symmetry	0.33		3.0		$\pm 10\text{mA} I_F, 10\text{V } V_{CE}$
Input to Output Isolation Voltage V_{ISO}	5300				V_{RMS}	See note 1
	7500				V_{PK}	See note 1
Input-output Isolation Resistance R_{ISO}	5×10^{10}				Ω	$V_{IO} = 500\text{V}$ (note 1)

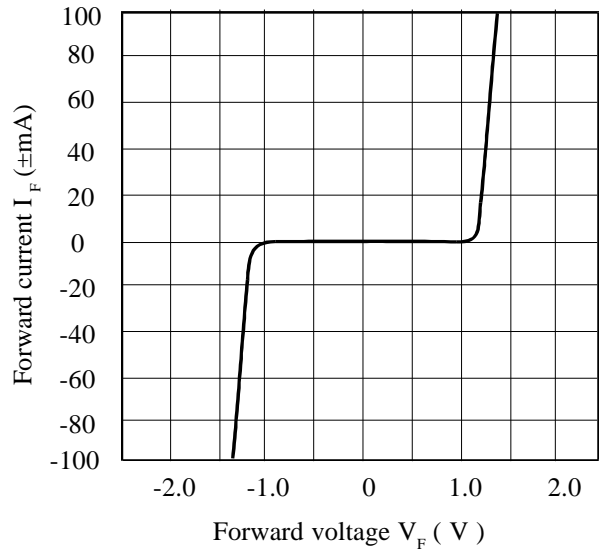
Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

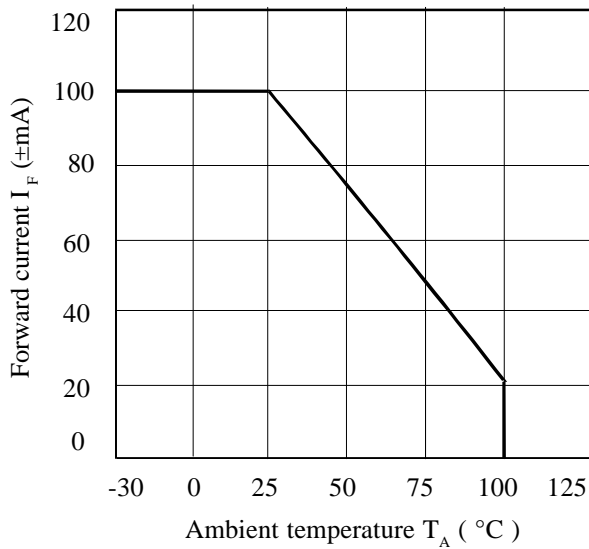
Collector Power Dissipation vs. Ambient Temperature



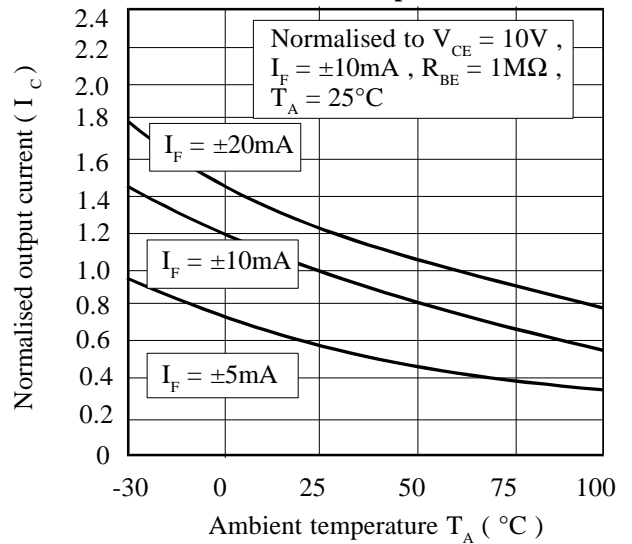
Forward Current vs. Forward Voltage



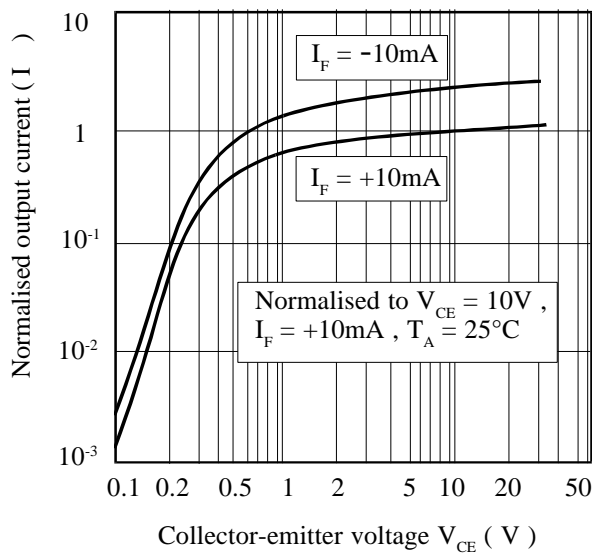
Forward Current vs. Ambient Temperature



Normalised Output Current vs. Ambient Temperature



Normalised Output Current vs. Collector-emitter Voltage



Normalised Output Current vs. Forward Current

